



## N-channel Enhancement Mode Mosfet

## CX010N06

### DESCRIPTION

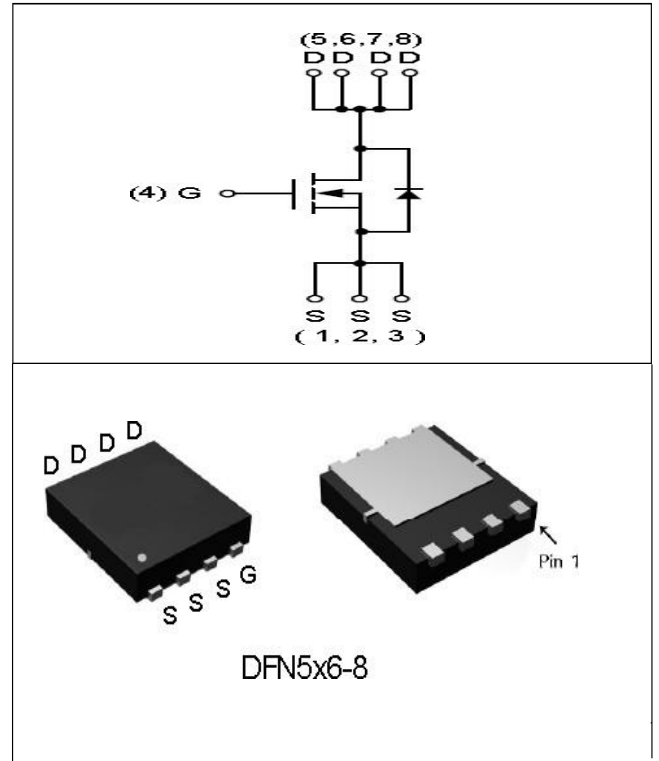
The CX010N06 is the high cell density trenched N-CH MOSFETs, which provide excellent  $R_{DS(ON)}$  and GATE charge for most of the synchronous Rectification

### GENERAL FEATURES

- $V_{DS} = 95V$   
 $R_{DS(ON)} = 6.1 m\Omega @ V_{GS} = 10V$
- Low  $R_{DS(on)}$  & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery

### Application

- PD charger
- Switching voltage regulator
- DC-DC convertor
- Switched mode power supply



### ■ Absolute Maximum Ratings ( $T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-source Voltage	$V_{DS}$	95	V	
Gate-source Voltage	$V_{GS}$	$\pm 20$	V	
Drain Current	$I_D$	$T_C = 25^\circ C$	110	A
		$T_C = 100^\circ C$	80	
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	280	A	
Total Power Dissipation	$P_D$	88	W	
Single Pulse Avalanche Energy <sup>B</sup>	EAS	78	mJ	
Thermal Resistance Junction-to-Case <sup>C</sup>	$R_{\theta JC}$	1.6	$^\circ C/W$	
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	30	$^\circ C/W$	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ C$	